

Low IR Schottky barrier diode

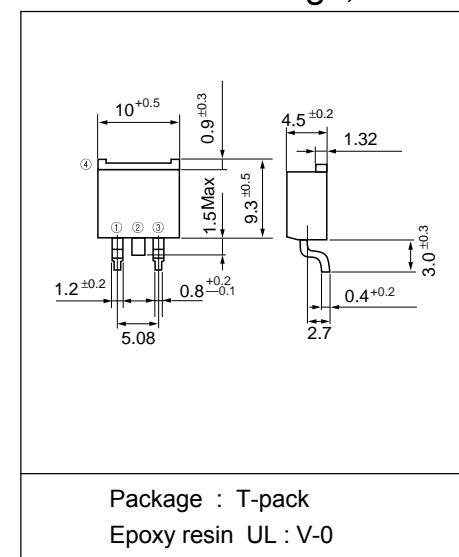
■ Features

- Low IR
- Low VF
- Center tap connection

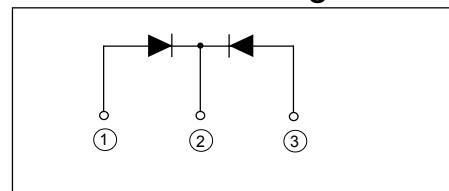
■ Applications

- High frequency operation
- DC-DC converters
- AC adapter

■ Outline drawings, mm



■ Connection diagram



■ Maximum ratings and characteristics

- Maximum ratings

Item	Symbol	Conditions	Rating	Unit
Repetitive peak surge reverse voltage	V _{RSM}	tw=500ns, duty=1/40	100	V
Repetitive peak reverse voltage	V _{RRM}		100	V
Isolating voltage	V _{iso}	Terminals-to-Case, AC.1min.	1500	V
Average output current	I _O	Square wave, duty=1/2 T _c =117°C	20 *	A
Non-repetitive surge current	I _{FSM}	Sine wave 10ms	145	A
non-repetitive reverse surge power dissipation	PRM	tw=10μs, T _j =25°C	660	W
Operating junction temperature	T _j		+150	°C
Storage temperature	T _{stg}		-40 to +150	°C

* Out put current of center tap full wave connection

- Electrical characteristics (at Ta=25°C Unless otherwise specified)

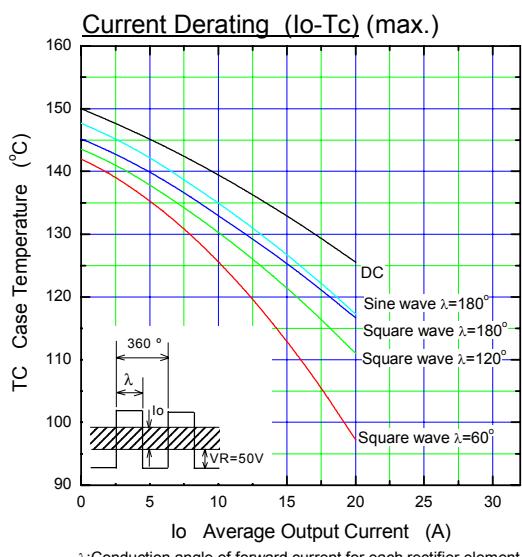
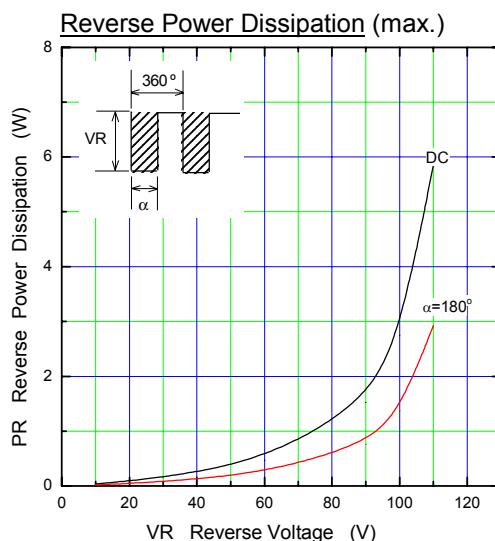
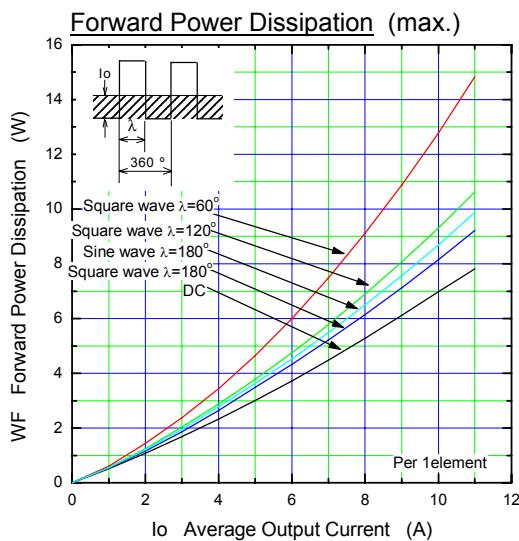
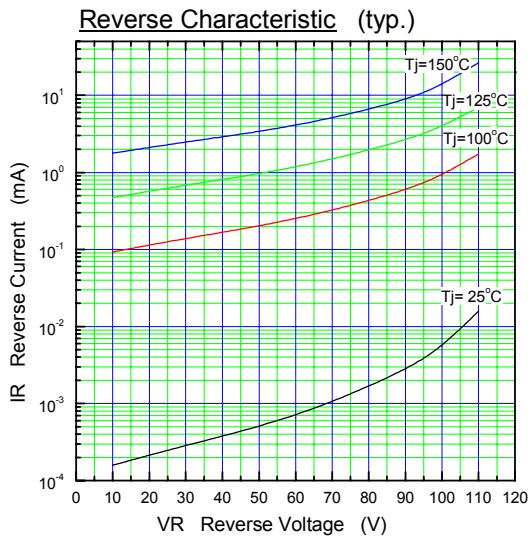
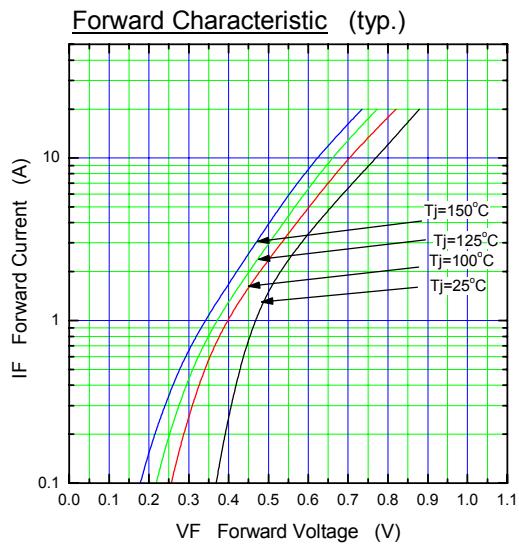
Item	Symbol	Conditions	Max.	Unit
Forward voltage **	V _F	I _F =10A	0.86	V
Reverse current **	I _R	V _R =100V	175	μA
Thermal resistance	R _{th(j-c)}	Junction to case	1.75	°C/W

**Rating per element

- Mechanical characteristics

Mounting torque	Recommended torque	0.3 to 0.5	N·m
Approximate mass		2	g

■ Characteristics



λ : Conduction angle of forward current for each rectifier element
Io: Output current of center-tap full wave connection

